

Analysis of the Radiation Monitoring System's Initial Data from the GEM Detectors at the CMS Experiment

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**GEM Detectors** 



**Radiation Monitoring System** 



System structure



Initial Data before RUN 3

### **CMS Experiment**

somewhere at the beginning of Long shutdown 2 (2019)



<u>CMS Muon System – 3 detection technologies</u>

- ✓ Drift tubes (DTs)
- $\checkmark$  Cathode Strip Chambers (CSCs)
- $\checkmark\,$  Resistive Plate Chambers (RPCs)









- LHC (RUN 3) instantaneous luminosity close to  $2x10^{34}$  cm<sup>-2</sup>s<sup>-1</sup>
- HL-LHC (RUN 4 ....) instantaneous luminosity close to  $(5-7.5)x10^{34}$  cm<sup>-2</sup>s<sup>-1</sup>
- HL-LHC background 5 x rates and 6 x total doses with respect to LHC
  - Exceed the primary design tolerances of different components of the detectors new assessment of the detectors electronics longevity, operation and performance

CMS Muon System goal – maintain excellent triggering, ID and measurement of muons during HL-LHC

### <u>CMS Forward Muon System Upgrade – Phase I</u>



5

100

30 40 50 60

L1 muon p\_ threshold [GeV]

20

6 7 8 910

### <u>GE1/1 detectors</u> <u>triple-GEM technology</u>

- > High rate capability, up to  $O(MHz/cm^2)$
- $\succ$  Efficiency > 97%
- > Space (time) resolution ~  $300\mu m$  (8ns)
- > Gas mixture  $Ar/CO_2$  70/30





Amplification region E field line Electron flow

#### Microscope picture of a GEM foil



assembly of the FE electronics



metal enclosure cover attachment



cooling circuit installation

SC assembly



**GE1/1 Installation** 

#### July-Oct 2019 $\rightarrow$ Negative endcap & July-Sept 2020 $\rightarrow$ Positive endcap



# RADIATION MONITORING SYSTEM IN GEM DETECTORS



## **Radiation Monitoring System in GEM Detectors**

A monitoring system, designed to measure the radiation dose and particle fluence around the GEM detectors, has been developed and installed in GE1/1 chambers.

The Radiation Monitoring (RadMon) System consists of 12 RadMon units with active radiation sensors.



#### Each RadMon unit contains:

- → RadFETs (Radiation sensitive Field Effective Transistors) absorbed dose (REM250, REM130)
- → p-i-n diodes 1 MeV neutron equivalent fluence (BPW34S, LBSD Si-1)
- $\rightarrow$  Thermistor
- $\rightarrow$  1k $\Omega$  resistor

Function	Туре	Device	Operating range	Sensitivity/ Resolution	I <sub>read</sub>
Total Dose Sensor (high doses)	RadFET	REM 250	A few $10^{-1}$ Gy up to > $2x10^4$ Gy	20 mV/Gy (initial)	160 µA
Total Dose Sensor (very high doses)	RadFET	REM 130	A few Gy up to > $2x10^5$ Gy	3 mV/Gy (initial)	160 µA
1 MeV n eq. Fluence Sensor (high sensitivity)	p-i-n diode	LBSD Si-1	$10^{10}{ m cm}^{-2}{ m up}$ to $2x10^{12}{ m cm}^{-2}$ (almost linear)	2.1x10 <sup>8</sup> cm <sup>-2</sup> /mV	10 mA
1 MeV n eq. Fluence Sensor (low sensitivity)	p-i-n diode	BPW34 S	$2x10^{12} \mathrm{cm}^{-2}$ up to $4x10^{14} \mathrm{cm}^{-2}$ (linear)	1x10 <sup>10</sup> cm <sup>-2</sup> /mV	1 mA
Temperature sensor	Thermisto r	NTC 10k	-55 °C up to 125 °C	0.1 °C	10 μΑ
Line checking	Resistor	1 k		1 %	160 µA

# RadFETs and p-i-n diodes have several advantages:

- $\checkmark$  Small detector sizes
- ✓ Immediate (online) readout
- ✓ Minimal power requirement

✓ Every RadMon unit has been inserted in metal bracket fixed on the GE1/1 cooling module (long chambers, wide region)

 $\checkmark$  6 RadMon units with active radiation sensors are installed in 6 GE1/1 long detectors in each endcap (totally 12 sensors)



### Dose and particle fluence measurement



Fluence  $(Si - 1) = (3 \times 10^{11} \times \Delta U - 4 \times 10^{10}) \times 0.62$ ,  $\Delta U < 4.1274$ 

Fluence  $(Si - 1) = (7 \times 10^{10} \times (\Delta U)^{1.9754}) \times 0.62$ ,  $\Delta U > 4.1274$ 

Dose (REM250)=  $\left(\frac{U_i - U_0}{A}\right)^{1/B}$ , A & B are known coefficients

Irradiation with high energetic hadrons can provoke accumulation of local defects in the RadFETs/p-i-n diodes.

The voltage drop across all radiation sensors is proportional to the measured radiation/particle fluence magnitude.

For the RadFETs the relation between the gate threshold voltage shift  $\Delta V_{\rm th}$  and the radiation dose D can be best approximated by  $\Delta V_{\rm th} = A \times D^{\rm B}$ , (resp.  $D = (\Delta V_{\rm th}/A)^{1/{\rm B}}$ ). The coefficients A and B depend on the RadFET type as well as on the measured dose range.

The shift of the p-i-n diodes forward voltage  $\Delta V_{\rm F}$  is proportional to the 1 MeV neutron equivalent fluence  $\Phi$  [cm<sup>-2</sup>]. The relation is generally linear –  $\Phi = c\Delta V_{\rm F}$ , where *c* depends of the diode type.

### **Temperature Dependence**

The plots contain the averaged data per hour for the LBSD Si-1/RadFET (Rem250) and thermistor data which are integrated in RadMon 3 unit installed in the bottom sector of the CMS Negative endcap.





- The uncertainty of threshold voltage of sensors is ±0.0018V considering both the precision of the ADC in the controllers and data averaging
- The uncertainty of thermistor measurements is estimated to be ±0.22°C
- > No presence of magnetic field

### Dependence on the CMS Magnetic Field

The plots contain the averaged data per hour for the LBSD Si-1/RadFET (Rem250) and the CMS Magnetic field during one week from the "warming up period of the CMS Magnet" performed in October 2021.





- The uncertainty of threshold voltage of sensors is ±0.0018V considering both the precision of the ADC in the controllers and data averaging
- The temperature during the presented period fluctuated within 0.3°C
- The p-i-n diode and RadFET are integrated in RadMon 6 unit installed in the top sector of the CMS Negative endcap.
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- Daily average threshold voltage values for the p-i-n diode (Si-1) and RadFET (Rem250) active sensors in relation to the temperature and the CMS magnetic field during the last ten months of LS2 (Aug 1 2021 until May 26 2022 inclusively) and the beginning of the LHC Commissioning period (27<sup>th</sup> May 2022 until 20<sup>th</sup> June 2022)
- > The uncertainty of threshold voltage of radiation sensors is evaluated to be  $\pm 0.0004$ V due to data averaging and precision of the ADC integrated in the controllers while the uncertainty of thermistor measurements is estimated to be  $\pm 0.1$ °C.
- > The increase of forward  $U_{th}$ (Si-1) at given forward current in magnetic field observed in p-i-n diodes can be attributed to magnetoresistance as well as to the increased charged carrier recombination [1]. The observed change of  $U_{th}$ (REM250) in magnetic field is due to similar effects as in p-i-n diodes.

- > The threshold voltage values of the active radiation sensors are well determined before the start of LHC RUN3:
  - Calibration (offset) of the voltage threshold for each sensor has been determined at the CMS magnetic field
  - > Temperature correction is required to achieve lowest possible uncertainty

> The radiation monitoring system of GEM is fully tested to measure the total dose and neutron flux in the area of the GE1/1 chambers installed at Station1 in the region of the endcaps.

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# **THANK YOU**

